## BD676, BD676A, BD678, BD678A, BD680, BD680A, BD682, BD682T

## Plastic Medium-Power Silicon PNP Darlingtons

This series of plastic, medium-power silicon PNP Darlington transistors can be used as output devices in complementary general-purpose amplifier applications.

## Features

- High DC Current Gain -

$$
\mathrm{h}_{\mathrm{FE}}=750(\mathrm{Min}) @ \mathrm{I}_{\mathrm{C}}=1.5 \text { and } 2.0 \mathrm{Adc}
$$

- Monolithic Construction
- BD676, 676A, 678, 678A, 680, 680A, 682 are complementary with BD675, 675A, 677, 677A, 679, 679A, 681
- BD678, 678A, 680, 680A are equivalent to MJE 700, 701, 702, 703
- $\mathrm{Pb}-$ Free Package are Available*


## MAXIMUM RATINGS

$\left.\begin{array}{|c|c|c|c|}\hline \text { Rating } & \text { Symbol } & \text { Value } & \text { Unit } \\ \hline \text { Collector-Emitter Voltage } \\ \text { BD676, BD676A } \\ \text { BD678, BD678A } \\ \text { BD680, BD680A } \\ \text { BD682 }\end{array}\right)$

## THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
| :---: | :---: | :---: | :---: |
| Thermal Resistance, <br> Junction-to-Case | $\mathrm{R}_{\text {өJC }}$ | 3.13 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

[^0]ON Semiconductor ${ }^{\circledR}$
http://onsemi.com

### 4.0 AMP DARLINGTON

 POWER TRANSISTORS PNP SILICON45, 60, 80, 100 VOLT, 40 WATT


TO-225AA CASE 77 STYLE 1


## ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

ELECTRICAL CHARACTERISTICS $\left(T_{C}=25^{\circ} \mathrm{C}\right.$ unless otherwise noted)

| Characteristic |  | Symbol | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| OFF CHARACTERISTICS |  |  |  |  |  |
| Collector-Emitter Breakdown Voltage (Note 1) $\left(I_{C}=50 \mathrm{mAdc}, \mathrm{I}_{\mathrm{B}}=0\right)$ | $\begin{aligned} & \text { BD676, 676A } \\ & \text { BD678, 678A } \\ & \text { BD680, 680A } \\ & \text { BD682 } \end{aligned}$ | $\mathrm{BV}_{\text {CEO }}$ | $\begin{gathered} \hline 45 \\ 60 \\ 80 \\ 100 \end{gathered}$ | - | Vdc |
| Collector Cutoff Current ( $\mathrm{V}_{\text {CE }}=$ Half Rated $\mathrm{V}_{\text {CEO }}, \mathrm{I}_{\mathrm{B}}=0$ ) |  | $I_{\text {CEE }}$ | - | 500 | $\mu \mathrm{Adc}$ |
| Collector Cutoff Current $\begin{aligned} & \left(V_{C B}=\text { Rated } B V_{C E O}, I_{E}=0\right) \\ & \left(V_{C B}=\text { Rated } B V_{C E O} \cdot I_{E}=0, T_{C}=100^{\circ} \mathrm{C}\right) \end{aligned}$ |  | $\mathrm{I}_{\text {cbo }}$ |  | $\begin{aligned} & 0.2 \\ & 2.0 \end{aligned}$ | mAdc |
| Emitter Cutoff Current ( $\mathrm{V}_{\mathrm{BE}}=5.0 \mathrm{Vdc}, \mathrm{I}_{\mathrm{C}}=0$ ) |  | $\mathrm{I}_{\text {EBO }}$ | - | 2.0 | mAdc |

## ON CHARACTERISTICS

| $\begin{aligned} & \text { DC Current Gain (Note 1) } \\ & \left(I_{C}=1.5 \mathrm{Adc}, \mathrm{~V}_{\mathrm{CE}}=3.0 \mathrm{Vdc}\right) \\ & \left(\mathrm{I}_{\mathrm{C}}=2.0 \mathrm{Adc}, \mathrm{~V}_{\mathrm{CE}}=3.0 \mathrm{Vdc}\right) \end{aligned}$ | $\begin{aligned} & \text { BD676, 678, 680, } 682 \\ & \text { BD676A, 678A, 680A } \end{aligned}$ | $h_{\text {FE }}$ | $\begin{aligned} & 750 \\ & 750 \end{aligned}$ |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\begin{aligned} & \text { Collector-Emitter Saturation Voltage (Note 1) } \\ & \left(I_{C}=1.5 \mathrm{Adc}, I_{\mathrm{B}}=30 \mathrm{mAdc}\right) \\ & \left(I_{\mathrm{C}}=2.0 \mathrm{Adc}, \mathrm{I}_{\mathrm{B}}=40 \mathrm{mAdc}\right) \end{aligned}$ | $\begin{aligned} & \text { BD678, 680, 682 } \\ & \text { BD676A, 678A, 680A } \end{aligned}$ | $\mathrm{V}_{\text {CE (sat) }}$ | - | $\begin{aligned} & 2.5 \\ & 2.8 \end{aligned}$ | Vdc |
| $\begin{gathered} \text { Base-Emitter On Voltage (Note 1) } \\ \left(I_{C}=1.5 \mathrm{Adc}, \mathrm{~V}_{\mathrm{CE}}=3.0 \mathrm{Vdc}\right) \\ \left(\mathrm{I}_{\mathrm{C}}=2.0 \mathrm{Adc}, \mathrm{~V}_{\mathrm{CE}}=3.0 \mathrm{Vdc}\right) \end{gathered}$ | $\begin{aligned} & \text { BD678, 680, 682 } \\ & \text { BD676A, 678A, 680A } \end{aligned}$ | $\mathrm{V}_{\mathrm{BE} \text { (on) }}$ | - | $\begin{aligned} & 2.5 \\ & 2.5 \end{aligned}$ | Vdc |

## DYNAMIC CHARACTERISTICS

| Small-Signal Current Gain ( $\left.\mathrm{I}_{\mathrm{C}}=1.5 \mathrm{Adc}, \mathrm{V}_{\mathrm{CE}}=3.0 \mathrm{Vdc}, \mathrm{f}=1.0 \mathrm{MHz}\right)$ | $\mathrm{h}_{\mathrm{fe}}$ | 1.0 | - | - |
| :--- | :--- | :--- | :--- | :--- |

1. Pulse Test: Pulse Width $\leq 300 \mu \mathrm{~s}$, Duty Cycle $\leq 2.0 \%$.


Figure 1. Power Temperature Derating

There are two limitations on the power handling ability of a transistor average junction temperature and secondary breakdown. Safe operating area curves indicate $I_{C}-V_{C E}$ limits of the transistor that must be observed for reliable operation; e.g., the transistor must not be subjected to greater dissipation than the curves indicate.


Figure 2. DC Safe Operating Area

At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by secondary breakdown.


Figure 3. Darlington Circuit Schematic

ORDERING INFORMATION

| Device | Package | Shipping |
| :--- | :--- | :--- |
| BD676 | TO-225AA | 500 Units / Box |
| BD676G | TO-225AA <br> (Pb-Free) | 500 Units / Box |
| BD676A | TO-225AA | 500 Units / Box |
| BD676AG | TO-225AA <br> (Pb-Free) | 500 Units / Box |
| BD678 | TO-225AA | 500 Units / Box |
| BD678G | TO-225AA <br> (Pb-Free) | 500 Units / Box |
| BD678A | TO-225AA <br> TO-225AA <br> (Pb-Free) | 500 Units / Box |
| BD678AG | TO-225AA | 500 Units / Box |
| BD680 | TO-225AA <br> (Pb-Free) | 500 Units / Box |
| BD680G | TO-225AA | 500 Units / Box |
| BD680A | TO-225AA <br> (Pb-Free) | 500 Units / Box |
| BD680AG | TO-225AA | 500 Units / Box |
| BD682 | TO-225AA <br> (Pb-Free) | 500 Units / Box |
| BD682G | TO-225AA | 500 Units / Box |
| BD682T | TO-225AA <br> (Pb-Free) | 50 Units / Rail |
| BD682TG | 50 Units / Rail |  |

## BD676, BD676A, BD678, BD678A, BD680, BD680A, BD682, BD682T

## PACKAGE DIMENSIONS

TO-225AA
CASE 77-09
ISSUE Z


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANS Y14.5M, 1982
2. $077-01$ THRU -08 OBSOLETE, NEW STANDARD 077-09.

|  | INCHES |  | MILLIMETERS |  |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| DIM | MIN | MAX | MIN | MAX |  |  |
| A | 0.425 | 0.435 | 10.80 | 11.04 |  |  |
| B | 0.295 | 0.305 | 7.50 | 7.74 |  |  |
| C | 0.095 | 0.105 | 2.42 | 2.66 |  |  |
| D | 0.020 | 0.026 | 0.51 | 0.66 |  |  |
| F | 0.115 | 0.130 | 2.93 |  |  |  |
| G | 0.094 BSC |  | 2.39 |  |  |  |
| H | 0.050 |  | 0.095 | 1.27 |  | 2.41 |
| J | 0.015 | 0.025 | 0.39 | 0.63 |  |  |
| K | 0.575 | 0.655 | 14.61 | 16.63 |  |  |
| M | $5^{\circ}$ TYP |  | $5^{\circ}$ TYP |  |  |  |
| Q | 0.148 | 0.158 | 3.76 | 4.01 |  |  |
| R | 0.045 | 0.065 | 1.15 | 1.65 |  |  |
| S | 0.025 | 0.035 | 0.64 | 0.88 |  |  |
| U | 0.145 | 0.155 | 3.69 | 3.93 |  |  |
| V | 0.040 | --- | 1.02 | --- |  |  |

STYLE 1:
PIN 1. EMITTER
2. COLLECTOR
3. BASE

[^1]
## PUBLICATION ORDERING INFORMATION

## LITERATURE FULFILLMENT

Literature Distribution Center for ON Semiconductor P.O. Box 61312, Phoenix, Arizona 85082-1312 USA

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N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center 2-9-1 Kamimeguro, Meguro-ku, Tokyo, Japan 153-0051 Phone: 81-3-5773-3850

ON Semiconductor Website: http://onsemi.com Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.


[^0]:    *For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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